

ABSTRACT

There are provided a phase shift mask having a small number of haze defects, that is, a phase shift mask
5 capable of sufficiently suppressing occurrence of haze, and a method for manufacturing the phase shift mask. A phase shift mask (100) according to the present embodiment includes a substrate (11), a phase shift film (12) that is formed on the substrate (11) and has a
10 circuit pattern, and a protective film (13) that is formed on an upper surface (12t) and a side surface (12s) of the phase shift film (12), in which the phase shift film (12) enables adjustment of each of phase and transmittance with respect to exposure light to be
15 transmitted to a predetermined extent, the protective film (13) contains at least one selected from a tantalum metal, a tantalum compound, a tungsten metal, a tungsten compound, a tellurium metal, or a tellurium compound, and when a film thickness of the phase shift film (12) is
20 denoted by d_1 and a film thickness of the protective film (13) is denoted by d_2 , d_2 is thinner than d_1 , and d_2 is 15 nm or less.

FIG. 2A and FIG. 2B